

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE01H14D uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

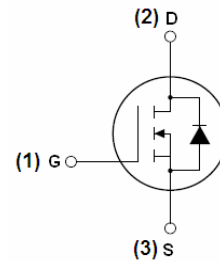
- $V_{DS} = 100V, I_D = 140A$   
 $R_{DS(ON)} < 5.5m\Omega @ V_{GS}=10V$  (Typ:4.9m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

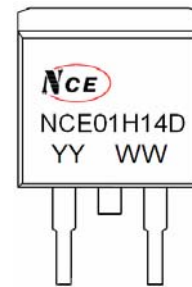
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

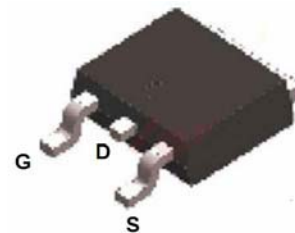
**100%  $\Delta V_{ds}$  TESTED!**



**Schematic diagram**



**Marking and pin assignment**



**TO-263-2L top view**

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01H14D	NCE01H14D	TO-263-2L	-	-	-

### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	140	A
Drain Current-Continuous( $T_C=100^\circ C$ )	$I_D(100^\circ C)$	97	A
Pulsed Drain Current	$I_{DM}$	550	A
Maximum Power Dissipation	$P_D$	330	W
Derating factor		2.2	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	1200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	0.45	$^{\circ}C/W$
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**Electrical Characteristics ( $T_C=25^{\circ}C$  unless otherwise noted)**

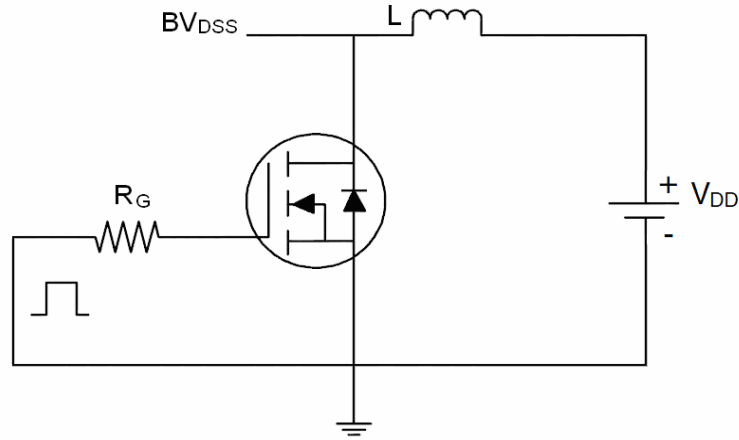
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3.2	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$	-	4.9	5.5	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=40A$	170	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	10500	-	PF
Output Capacitance	$C_{OSS}$		-	914	-	PF
Reverse Transfer Capacitance	$C_{RSS}$		-	695	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=65V, I_D=40A$ $V_{GS}=10V, R_{GEN}=2.5\Omega$	-	25	-	nS
Turn-on Rise Time	$t_r$		-	100	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	65	-	nS
Turn-Off Fall Time	$t_f$		-	77	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=44V, I_D=40A,$ $V_{GS}=10V$	-	120	-	nC
Gate-Source Charge	$Q_{GS}$		-	30	-	nC
Gate-Drain Charge	$Q_{gd}$		-	35	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=40A$	-	0.85	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	40	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = 40A$ $di/dt = 100A/\mu s$ (Note 3)	-	45	70	nS
Reverse Recovery Charge	$Q_{rr}$		-	80	120	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

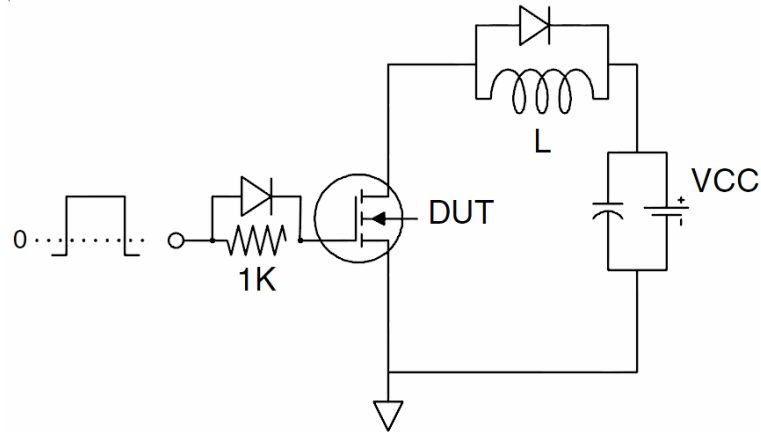
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, L=1mH, R_g=25\Omega$

**Test Circuit**

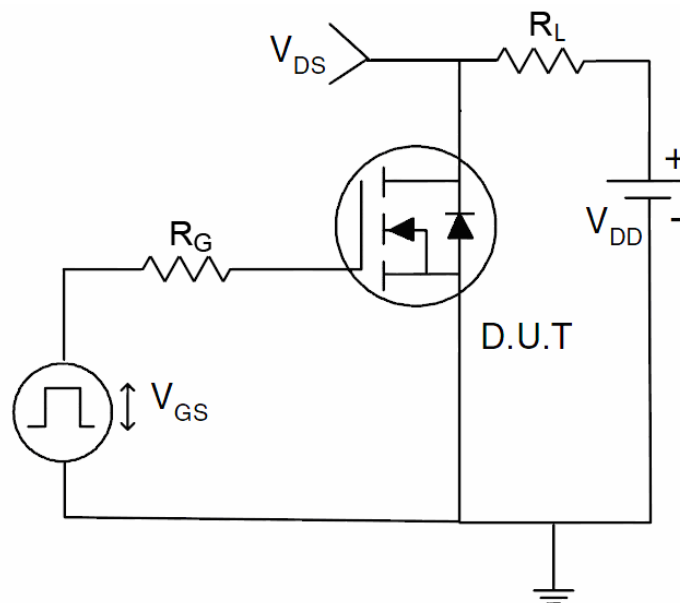
**1) E<sub>AS</sub> test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics (Curves)

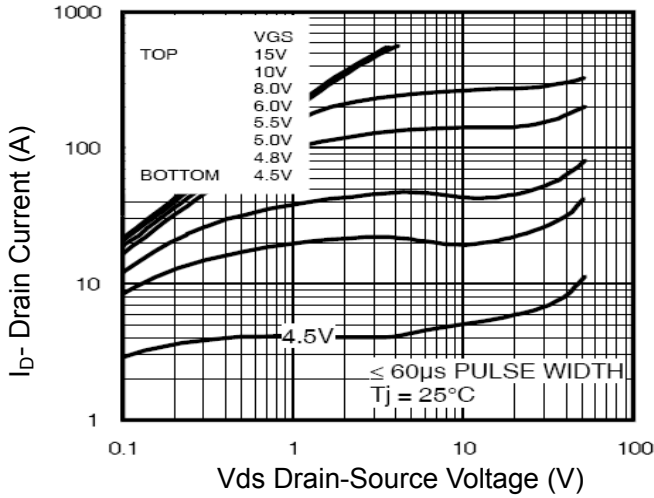


Figure 1 Output Characteristics

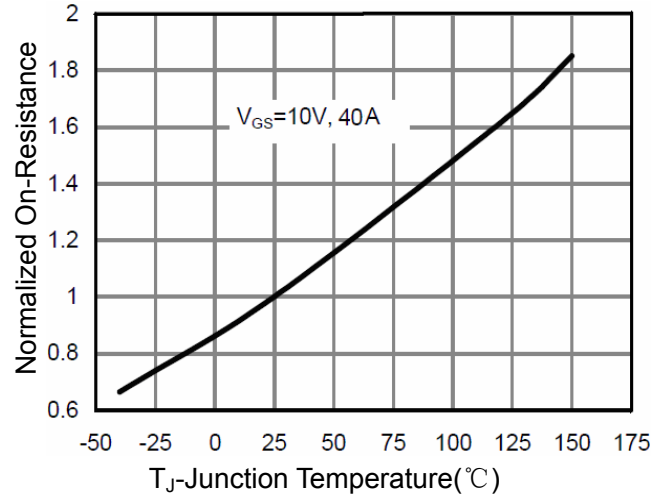


Figure 4 Rdson-Junction Temperature

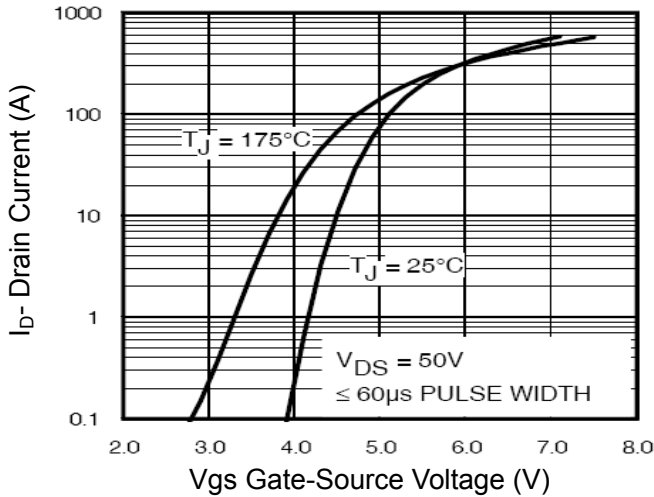


Figure 2 Transfer Characteristics

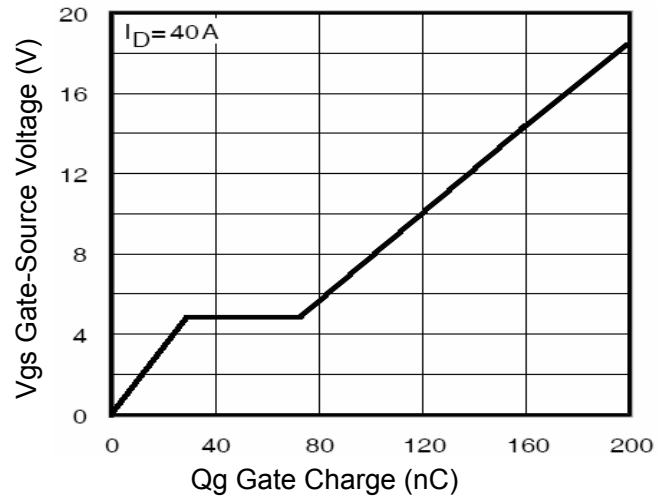


Figure 5 Gate Charge

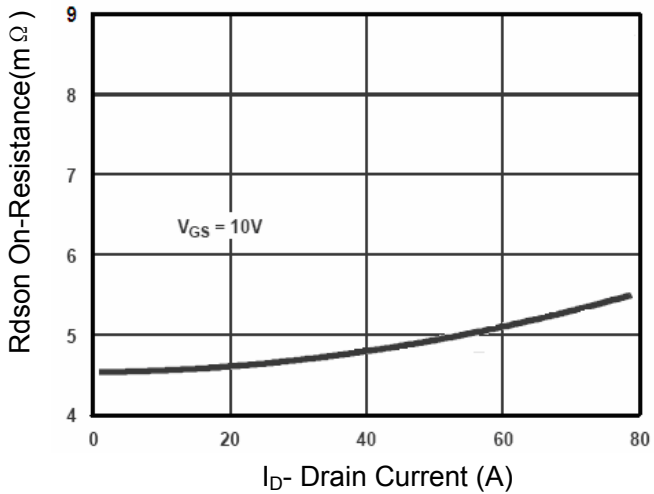


Figure 3 Rdson- Drain Current

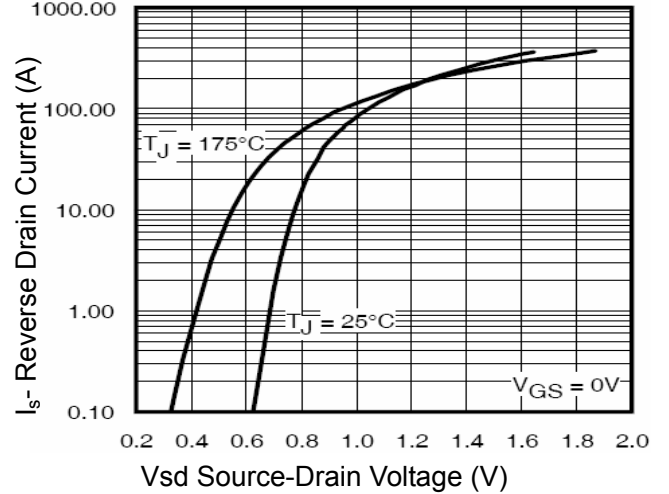


Figure 6 Source- Drain Diode Forward

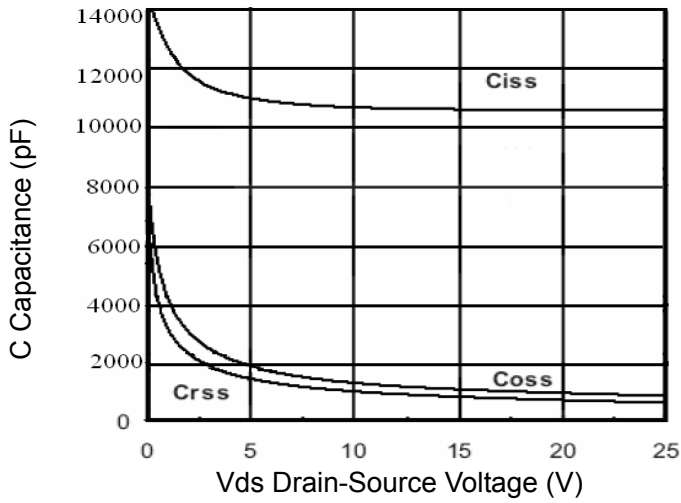


Figure 7 Capacitance vs Vds

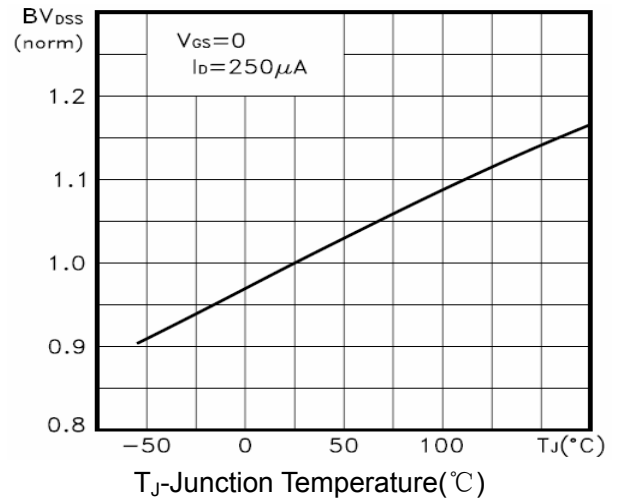


Figure 9  $BV_{DSS}$  vs Junction Temperature

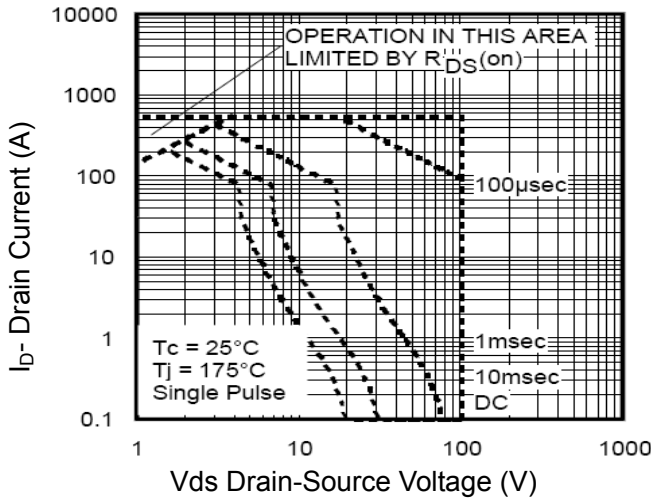


Figure 8 Safe Operation Area

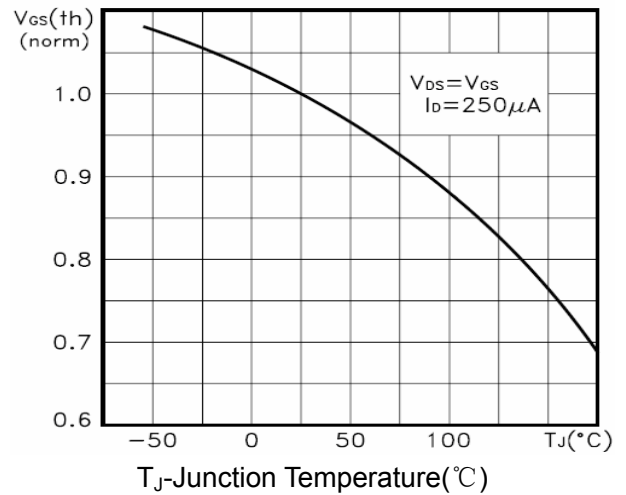


Figure 10  $V_{GS(th)}$  vs Junction Temperature

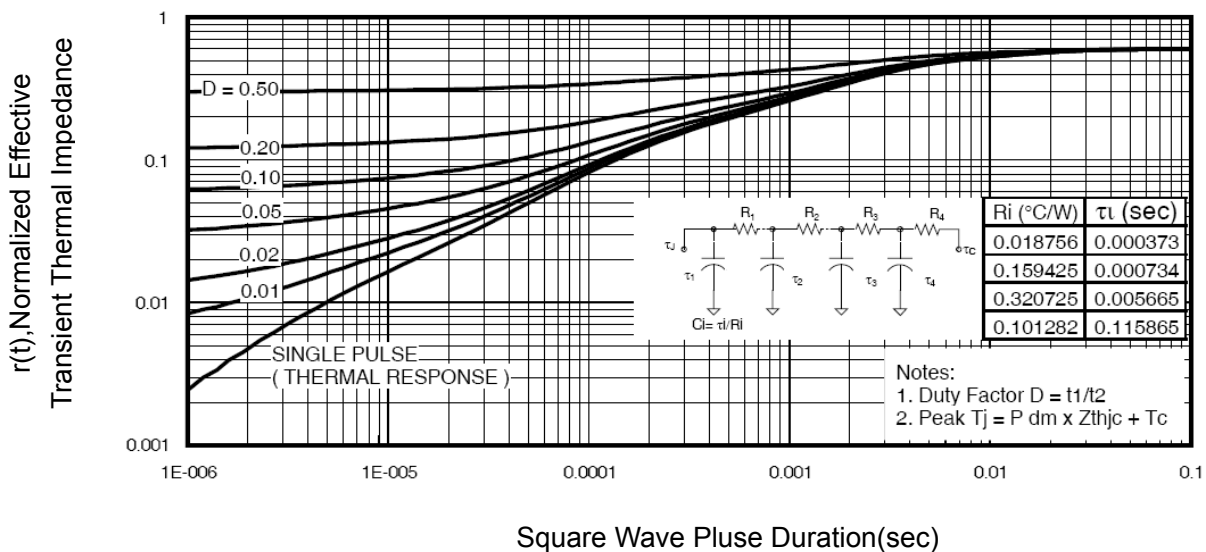
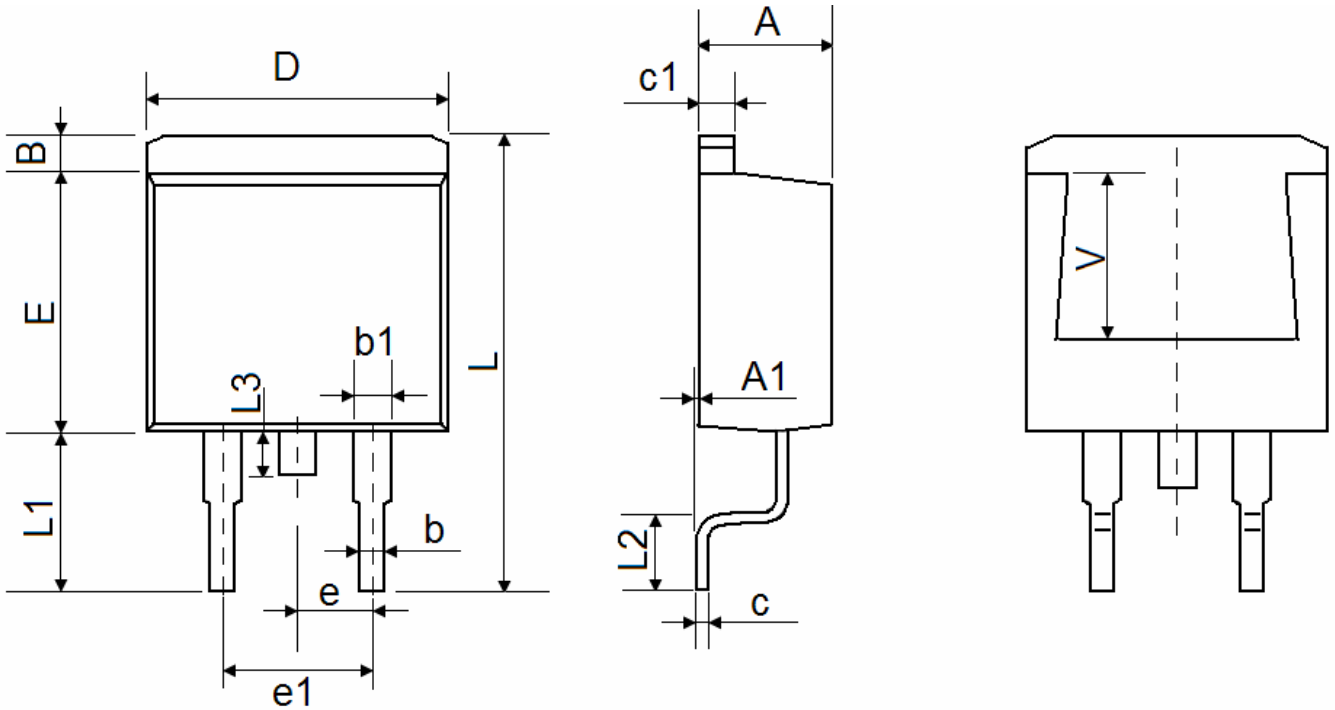


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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